



STD2LN60K3, STF2LN60K3, STU2LN60K3

N-channel 600 V, 4 Ω typ., 2 A SuperMESH3™ Power MOSFET
in DPAK, TO-220FP and IPAK packages

Datasheet — production data

Features

Order codes	V _{DSS}	R _{DS(on) max}	I _D	P _{TOT}
STD2LN60K3	600 V	< 4.5 Ω	2 A	45 W
STF2LN60K3				20 W
STU2LN60K3				45 W

- 100% avalanche tested
- Extremely high dv/dt capability
- Very low intrinsic capacitance
- Improved diode reverse recovery characteristics
- Zener-protected

Applications

- Switching applications

Description

These SuperMESH3™ Power MOSFETs are the result of improvements applied to STMicroelectronics' SuperMESH™ technology, combined with a new optimized vertical structure. These devices boast an extremely low on-resistance, superior dynamic performance and high avalanche capability, rendering them suitable for the most demanding applications.

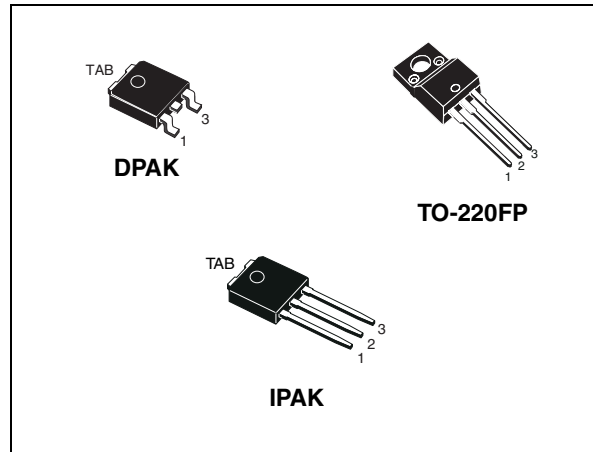


Figure 1. Internal schematic diagram

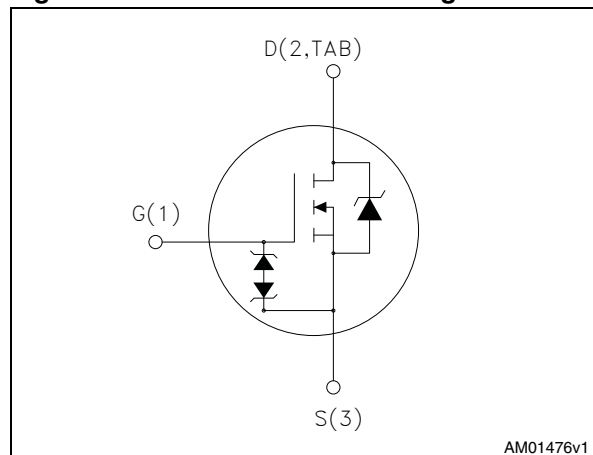


Table 1. Device summary

Order codes	Marking	Package	Packaging
STD2LN60K3	2LN60K3	DPAK	Tape and reel
STF2LN60K3		TO-220FP	Tube
STU2LN60K3		IPAK	

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value			Unit
		DPAK	TO-220FP	IPAK	
V_{DS}	Drain-source voltage	600			V
V_{GS}	Gate- source voltage	± 30			V
I_D	Drain current (continuous) at $T_C = 25\text{ °C}$	2	2 ⁽¹⁾	2	A
I_D	Drain current (continuous) at $T_C = 100\text{ °C}$	1.26	1.26 ⁽¹⁾	1.26	A
I_{DM} ⁽²⁾	Drain current (pulsed)	8	8 ⁽¹⁾	8	A
P_{TOT}	Total dissipation at $T_C = 25\text{ °C}$	45	20	45	W
	Derating factor	0.36	0.16	0.36	W/°C
$V_{ESD(G-S)}$	Gate source ESD (HBM-C = 100 pF, R = 1.5 kΩ)	2500			V
dv/dt ⁽³⁾	Peak diode recovery voltage slope	12			V/ns
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; $T_C = 25\text{ °C}$)		2500		V
T_{stg}	Storage temperature	-55 to 150			°C
T_j	Max. operating junction temperature	150			°C

1. Limited by package
2. Pulse width limited by safe operating area
3. $I_{SD} \leq 2\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, peak $V_{DS} < V_{(BR)DSS}$

Table 3. Thermal data

Symbol	Parameter	Value			Unit
		DPAK	TO-220FP	IPAK	
$R_{thj-case}$	Thermal resistance junction-case max	2.78	6.25	2.78	°C/W
$R_{thj-pcb}$	Thermal resistance junction-pcb max	50			°C/W
$R_{thj-amb}$	Thermal resistance junction-amb max		62.5	100	°C/W

Table 4. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j max)	2	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ °C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	80	mJ

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 5. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0$	600			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 600\text{ V}$ $V_{DS} = 600\text{ V}$, $T_C = 125\text{ °C}$			1 50	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 50\text{ }\mu\text{A}$	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 1\text{ A}$		4	4.5	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 50\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	235	-	pF
C_{oss}	Output capacitance			22		pF
C_{rss}	Reverse transfer capacitance			3.5		pF
$C_{o(tr)}^{(1)}$	Eq. capacitance time related	$V_{GS} = 0$, $V_{DS} = 0\text{ to }480\text{ V}$	-	14	-	pF
$C_{o(er)}^{(2)}$	Eq. capacitance energy related			10		pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	7	-	Ω
Q_g	Total gate charge	$V_{DD} = 480\text{ V}$, $I_D = 1\text{ A}$, $V_{GS} = 10\text{ V}$ (see Figure 18)	-	12	-	nC
Q_{gs}	Gate-source charge			1.8		nC
Q_{gd}	Gate-drain charge			7.7		nC

- $C_{oss\text{ eq.}}$ time related is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}
- $C_{oss\text{ eq.}}$ energy related is defined as a constant equivalent capacitance giving the same stored energy as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$, $I_D = 1\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 17)		10		ns
t_r	Rise time			8.5		ns
$t_{d(off)}$	Turn-off-delay time			23.5		ns
t_f	Fall time			21		ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current				2	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				8	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 2\text{ A}$, $V_{GS} = 0$			1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 2\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ (see Figure 22)		200		ns
Q_{rr}	Reverse recovery charge				800	nC
I_{RRM}	Reverse recovery current				8	A
t_{rr}	Reverse recovery time	$I_{SD} = 2\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 22)		230		ns
Q_{rr}	Reverse recovery charge				950	nC
I_{RRM}	Reverse recovery current				8.5	A

1. Pulse width limited by safe operating area.
2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%

Table 9. Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$BV_{GSO}^{(1)}$	Gate-source breakdown voltage	$I_{gs} = \pm 1\text{ mA}$ (open drain)	30		-	V

1. The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for DPAK and IPAK

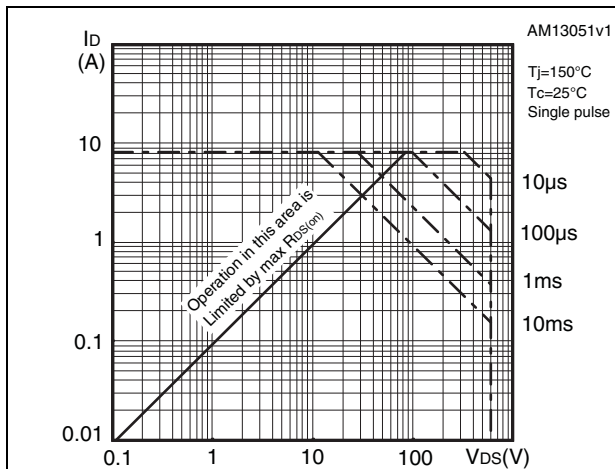


Figure 3. Thermal impedance for DPAK and IPAK

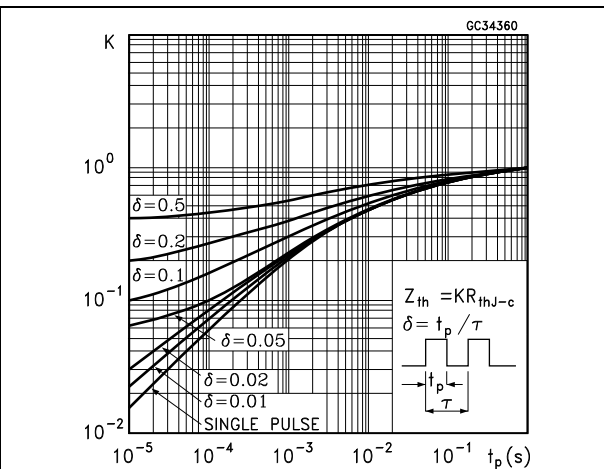


Figure 4. Safe operating area for TO-220FP

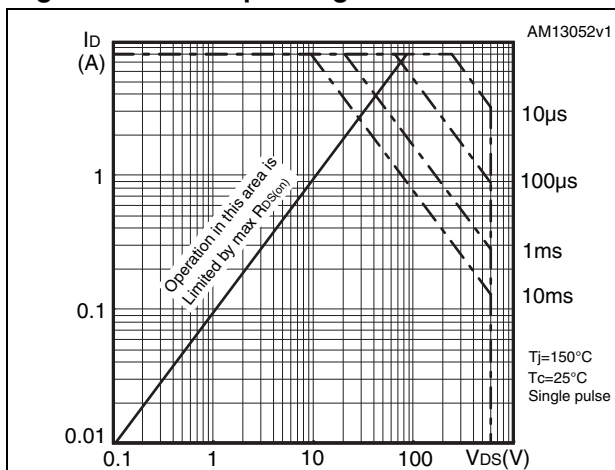


Figure 5. Thermal impedance for TO-220FP

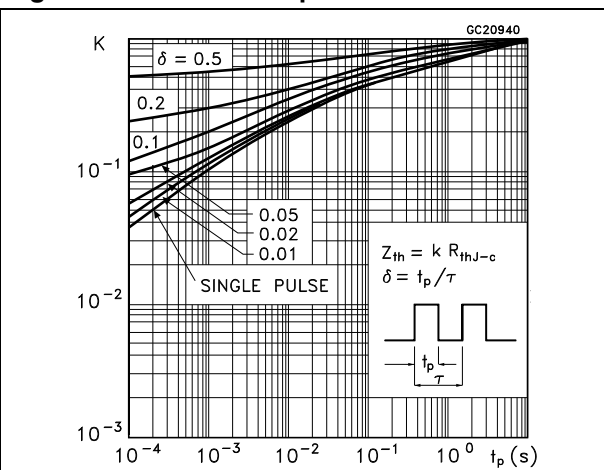


Figure 6. Output characteristics

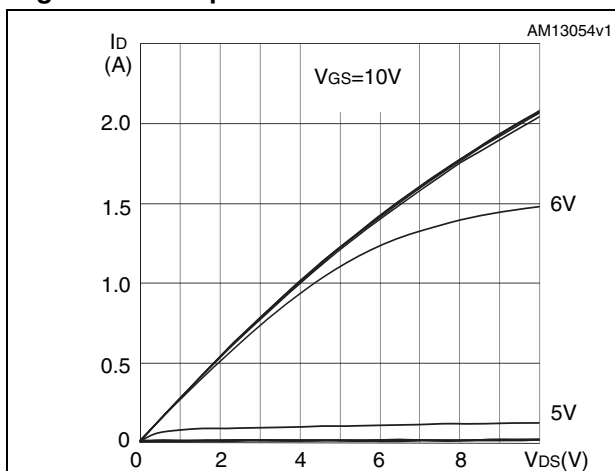


Figure 7. Transfer characteristics

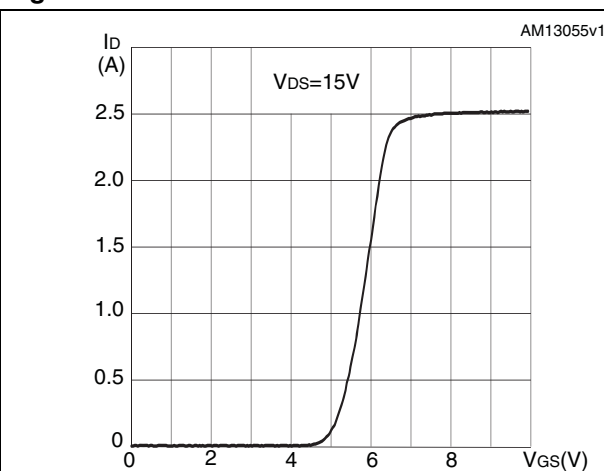


Figure 8. Gate charge vs gate-source voltage **Figure 9. Static drain-source on-resistance**

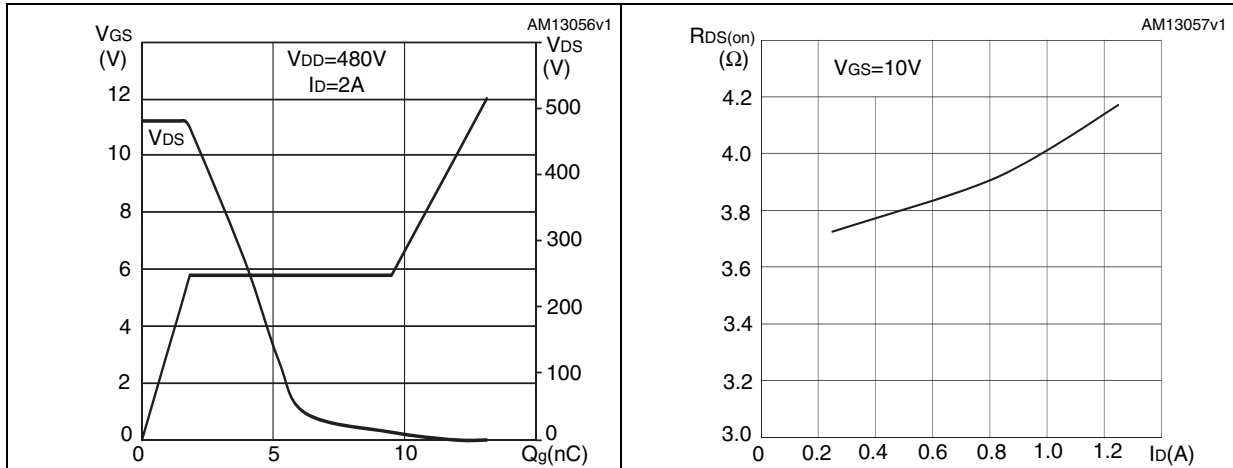


Figure 10. Capacitance variations **Figure 11. Output capacitance stored energy**

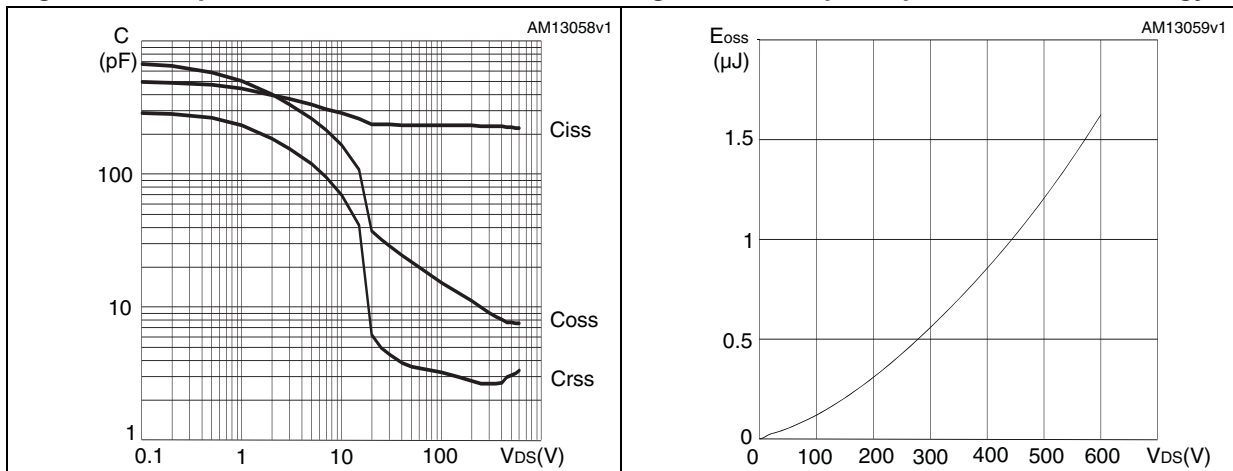


Figure 12. Normalized gate threshold voltage vs temperature **Figure 13. Normalized on-resistance vs temperature**

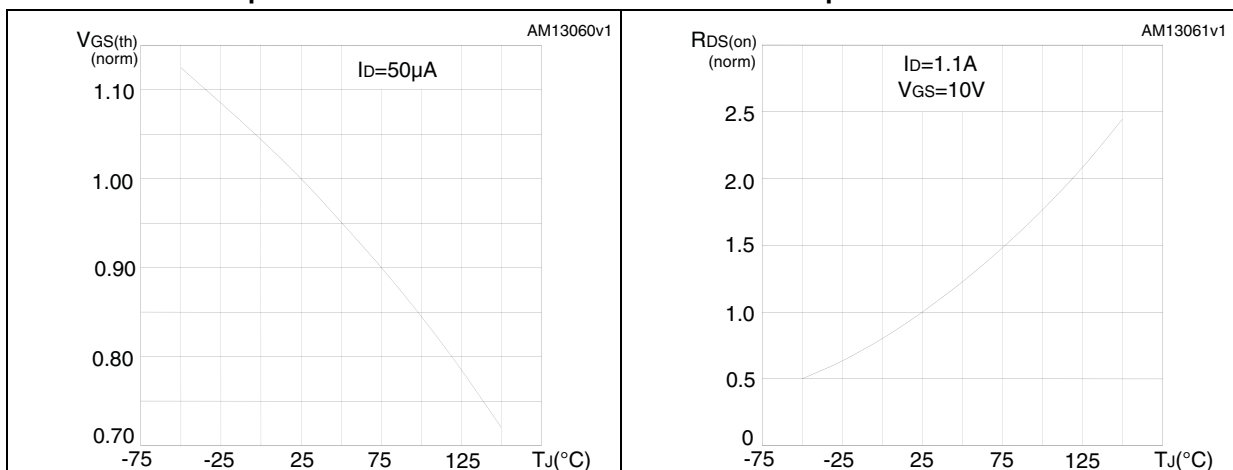


Figure 14. Normalized BV_{DSS} vs temperature

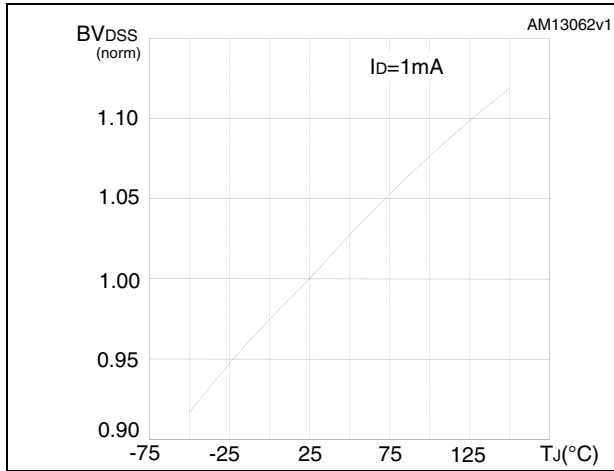


Figure 15. Source-drain diode forward characteristics

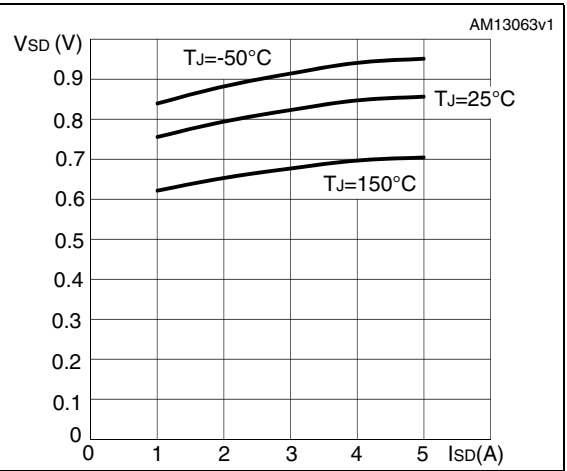
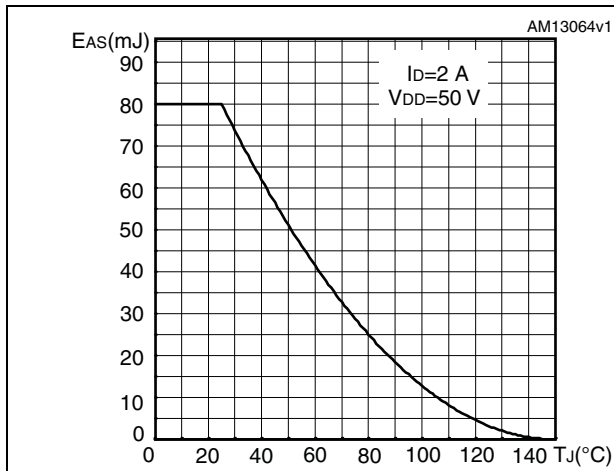


Figure 16. Maximum avalanche energy vs temperature



3 Test circuits

Figure 17. Switching times test circuit for resistive load

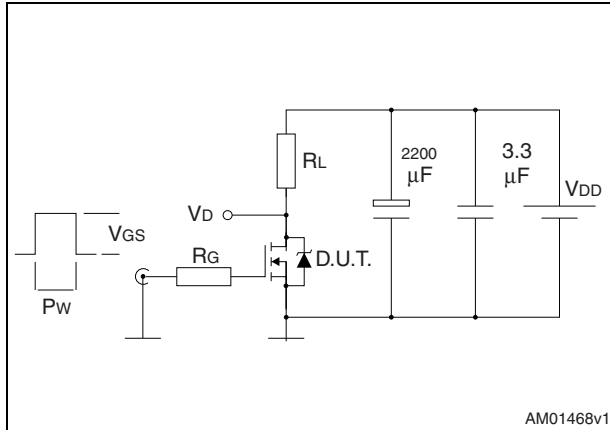


Figure 18. Gate charge test circuit

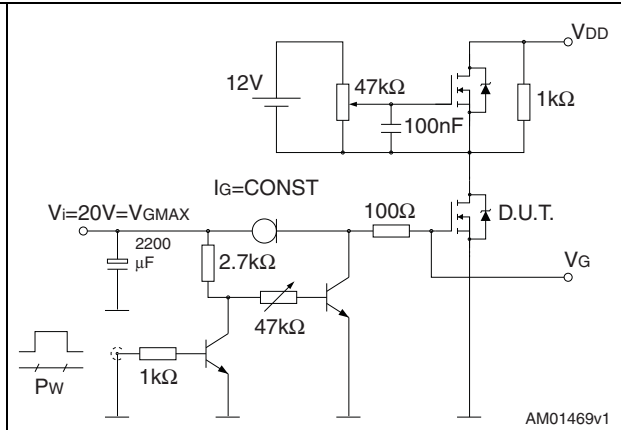


Figure 19. Test circuit for inductive load switching and diode recovery times

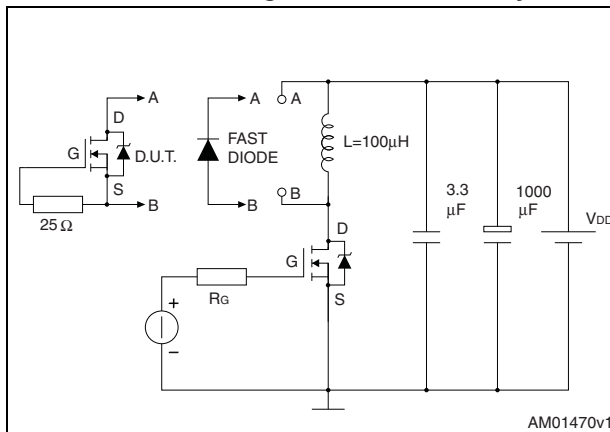


Figure 20. Unclamped Inductive load test circuit

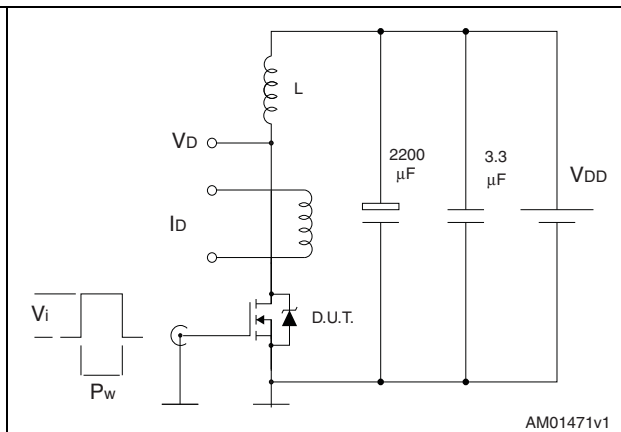


Figure 21. Unclamped inductive waveform

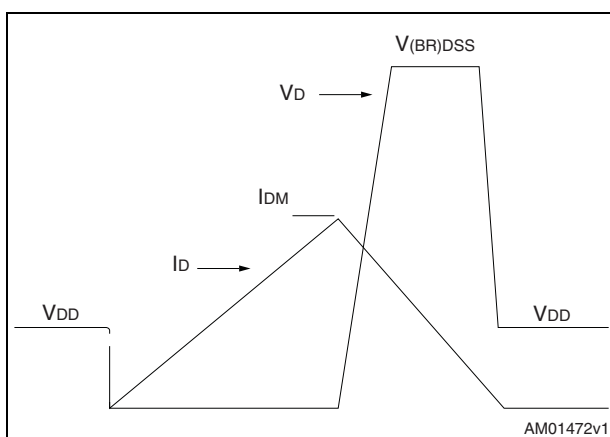
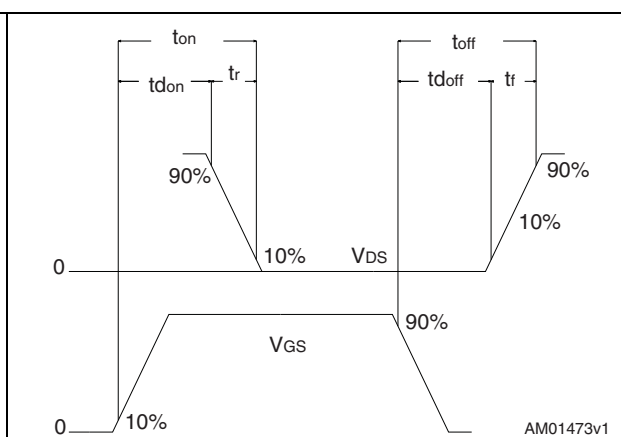


Figure 22. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 10. DPAK (TO-252) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°

Figure 23. DPAK (TO-252) drawing

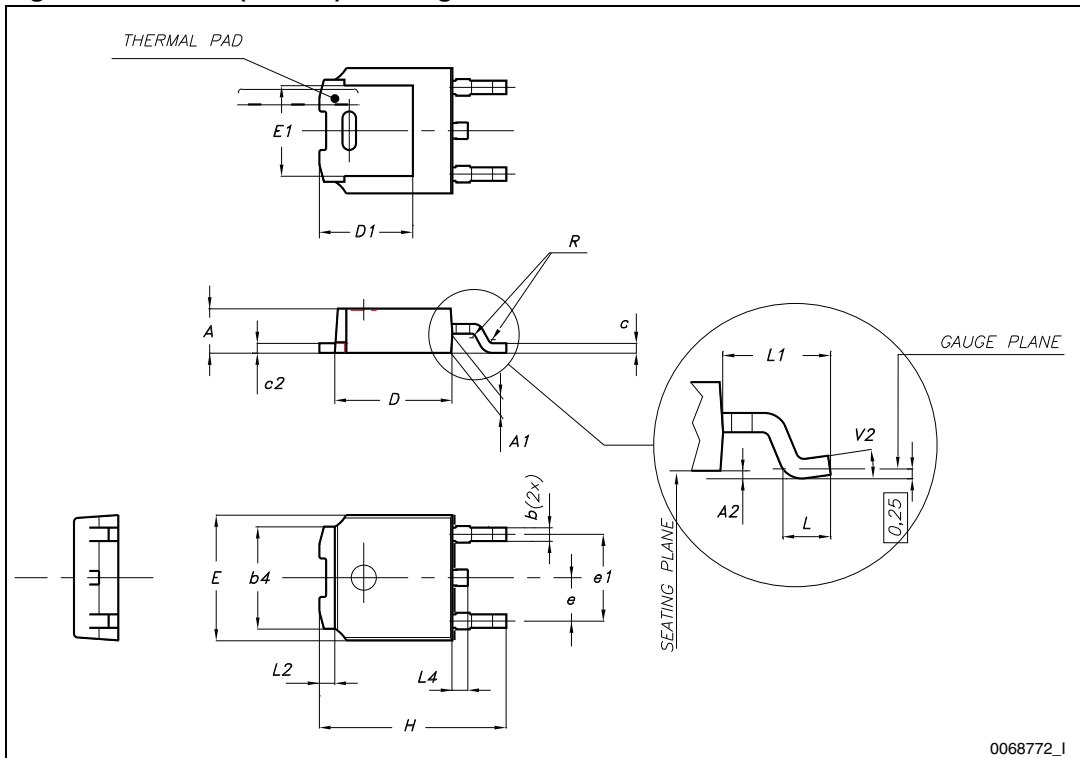
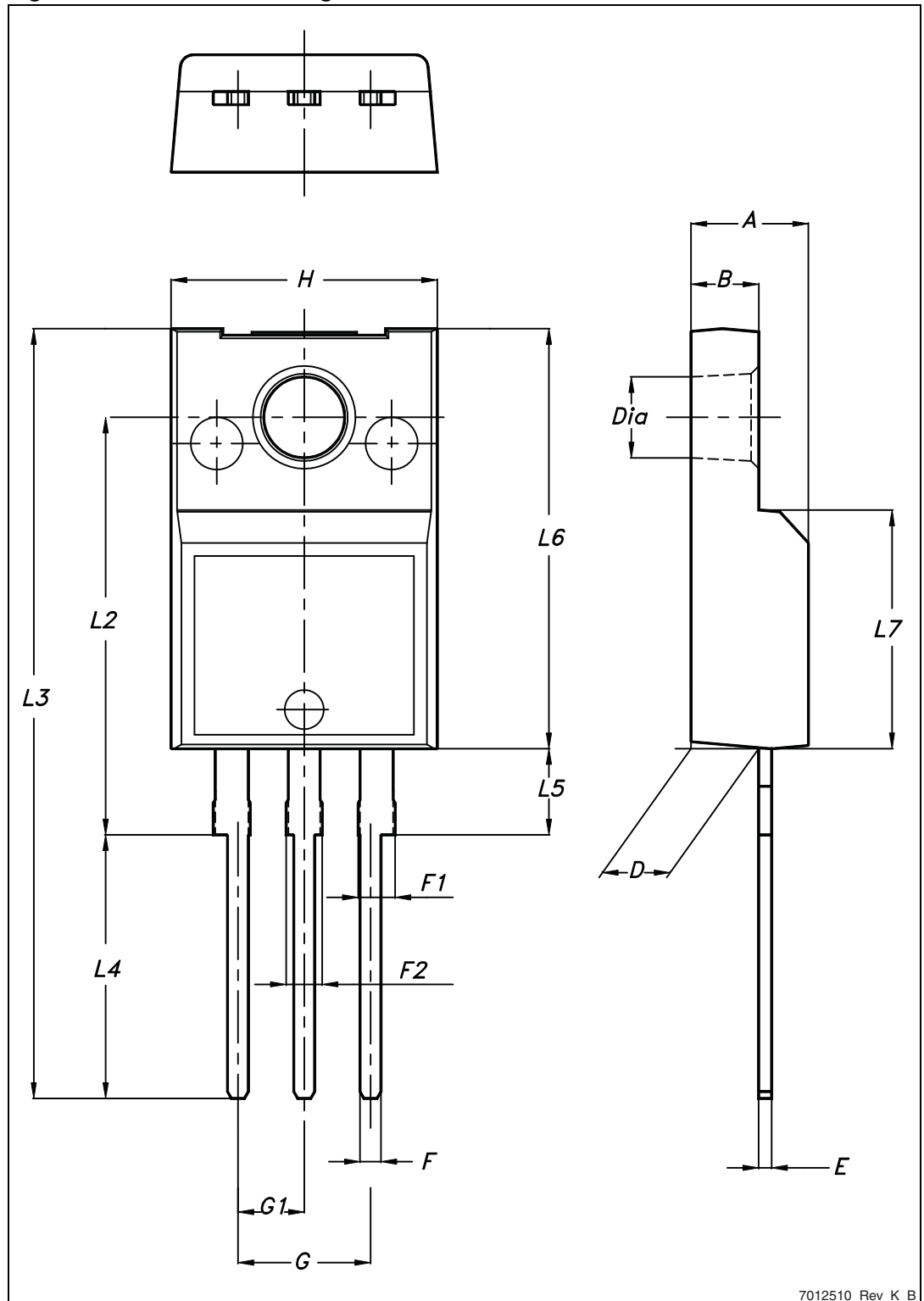


Table 11. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 24. TO-220FP drawing

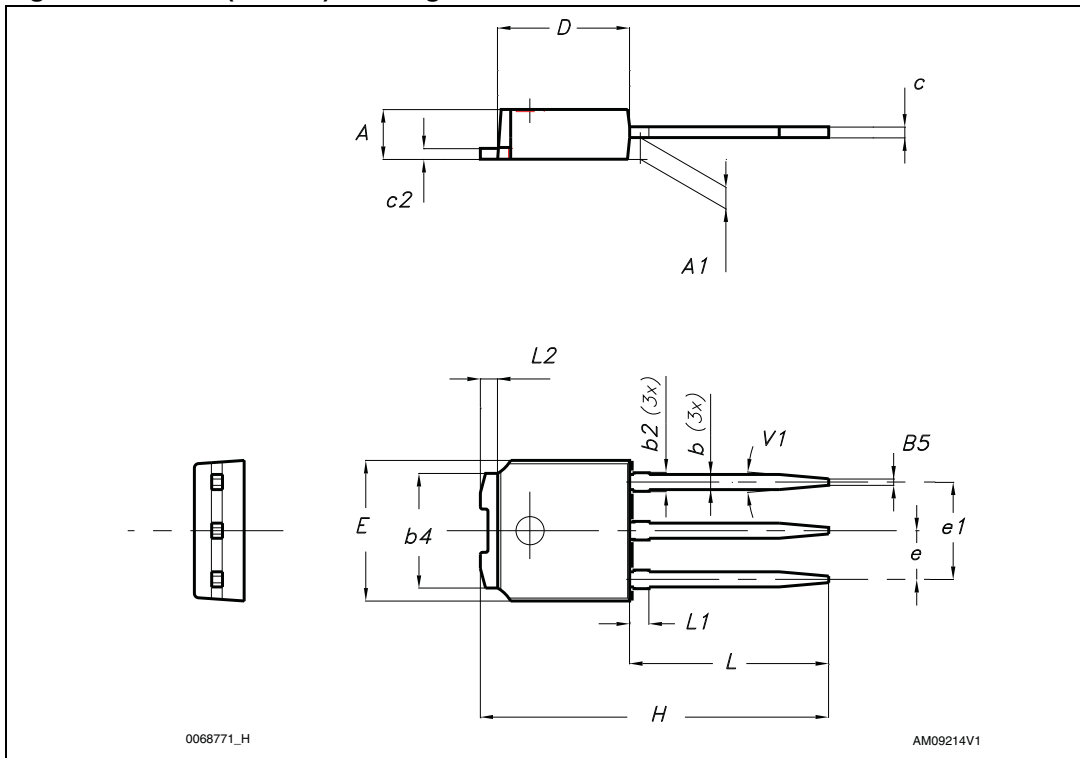


7012510_Rev_K_B

Table 12. IPAK (TO-251) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
B5		0.3	
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
L1	0.80		1.20
L2		0.80	1.00
V1		10 °	

Figure 25. IPAK (TO-251) drawing

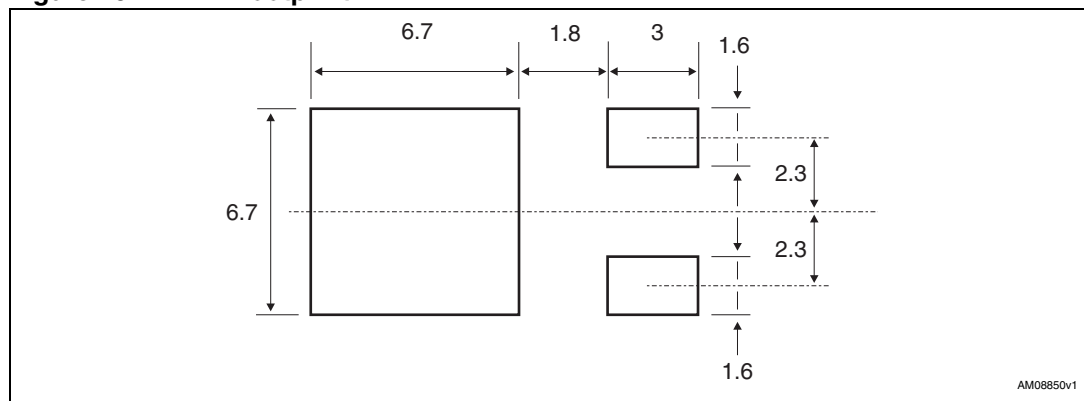


5 Packaging mechanical data

Table 13. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Figure 26. DPAK footprint^(a)



a. All dimension are in millimeters

Figure 27. Tape for DPAK (TO-252)

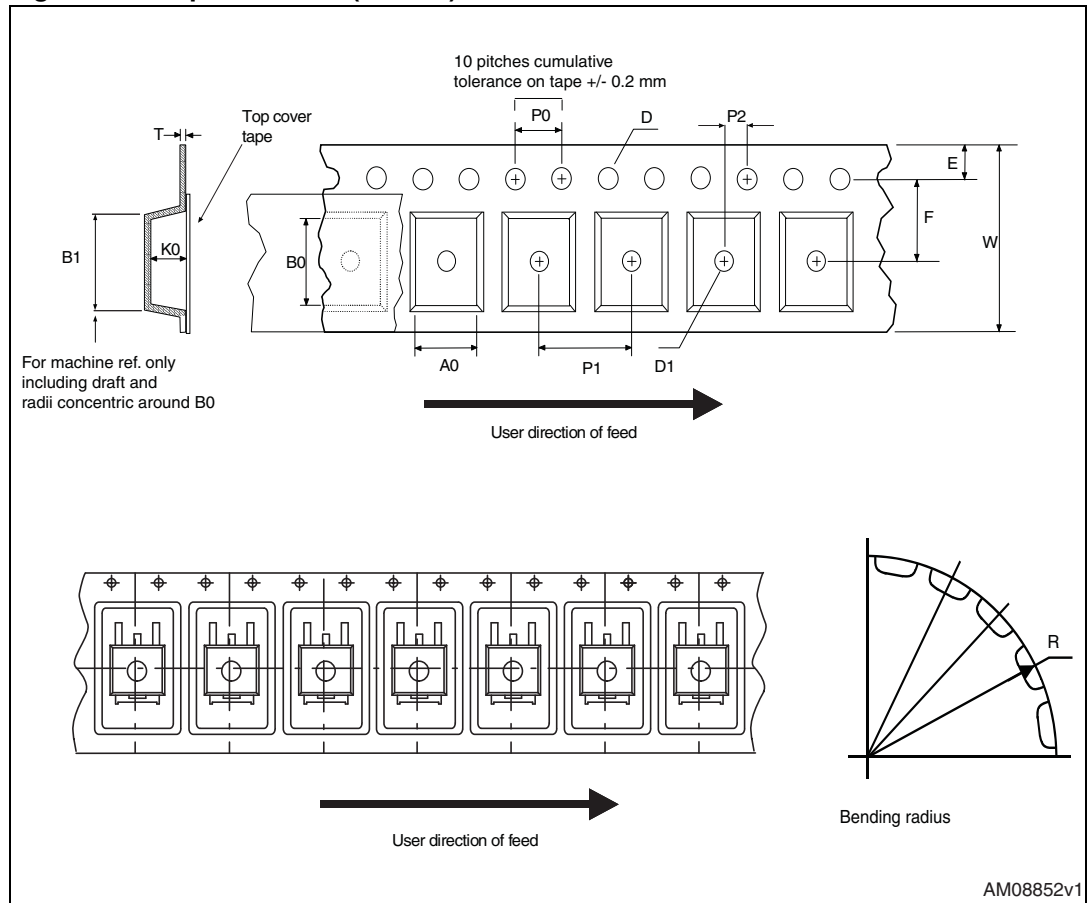
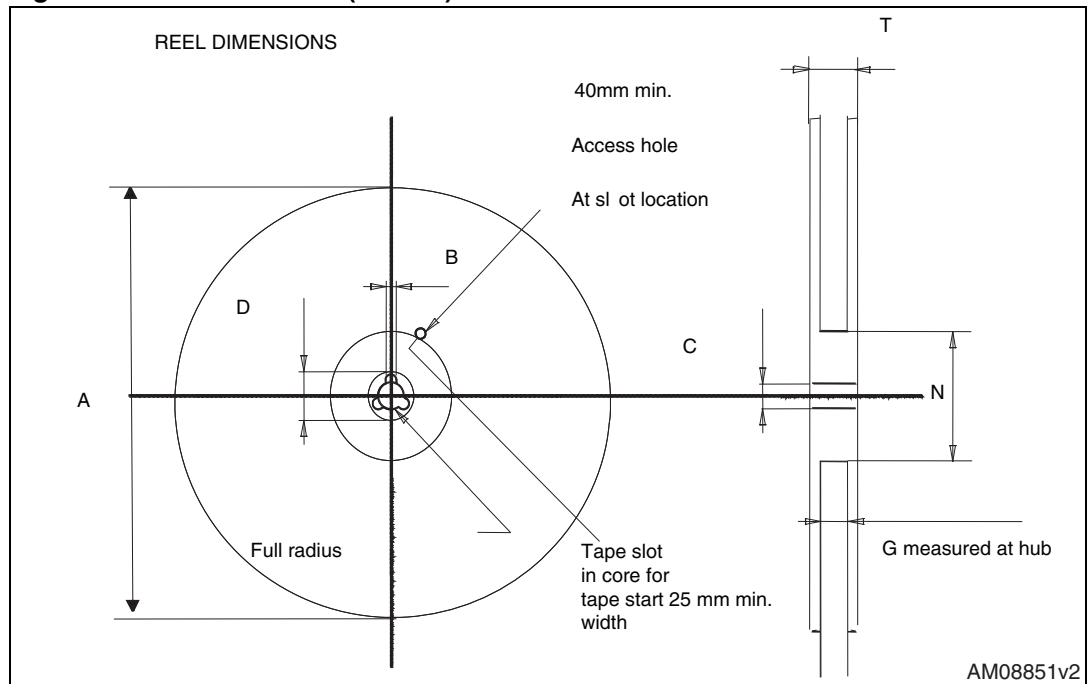


Figure 28. Reel for DPAK (TO-252)



6 Revision history

Table 14. Document revision history

Date	Revision	Changes
05-Jul-2012	1	First release.

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